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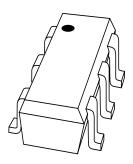
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PUMT1 PNP general purpose double transistor

Product data sheet Supersedes data of 1999 Apr 14 2001 Dec 19



NXP Semiconductors Product data sheet

PNP general purpose double transistor

PUMT1

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 40 V)
- Reduces number of components and boardspace.

APPLICATIONS

• General purpose switching and amplification.

DESCRIPTION

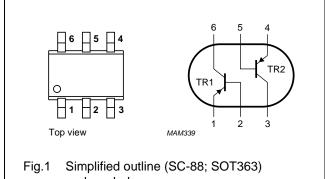
Two independently operating PNP transistors in an SC-88; SOT363 plastic package. NPN complement: PUMX1.

MARKING

TYPE NUMBER	MARKING CODE
PUMT1	FtF

PINNING

PIN	DESCRIPTION		
1, 4	emitter	TR1; TR2	
2, 5	base	TR1; TR2	
3, 6	collector	TR2; TR1	



and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	PARAMETER CONDITIONS		MAX.	UNIT	
Per transist	Per transistor					
V _{CBO}	collector-base voltage	open emitter	-	-50	V	
V_{CEO}	collector-emitter voltage	open base	_	-40	V	
V_{EBO}	emitter-base voltage	open collector	_	-5	V	
I _C	collector current (DC)		_	-100	mA	
I _{CM}	peak collector current		-	-200	mA	
I _{BM}	peak base current		-	-200	mA	
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	_	200	mW	
T _{stg}	storage temperature		-65	+150	°C	
Tj	junction temperature		-	150	°C	
T _{amb}	operating ambient temperature		-65	+150	°C	
Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	300	mW	

Note

1. Device mounted on an FR4 printed-circuit board.

2001 Dec 19 2 NXP Semiconductors Product data sheet

PNP general purpose double transistor

PUMT1

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per device				
R _{th j-a}	thermal resistance from junction to ambient	note 1	416	K/W

Note

1. Device mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 T_{amb} = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transist	or				
I _{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -30 \text{ V}$	_	-100	nA
		$I_E = 0$; $V_{CB} = -30 \text{ V}$; $T_j = 150 ^{\circ}\text{C}$	_	-10	μΑ
I _{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -4 \text{ V}$	_	-100	nA
h _{FE}	DC current gain	$I_C = -1 \text{ mA}; V_{CE} = -6 \text{ V}$	120	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = -5 \text{ mA}; \text{ note 1}$	_	-200	mV
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = -12 \text{ V}$; $f = 1 \text{ MHz}$	_	2.2	pF
f _T	transition frequency	$I_C = -2 \text{ mA}; V_{CE} = -12 \text{ V}; f = 100 \text{ MHz}$	100	_	MHz

Note

1. Pulse test: $t_p \leq 300~\mu s;~\delta \leq 0.02.$

2001 Dec 19 3

NXP Semiconductors Product data sheet

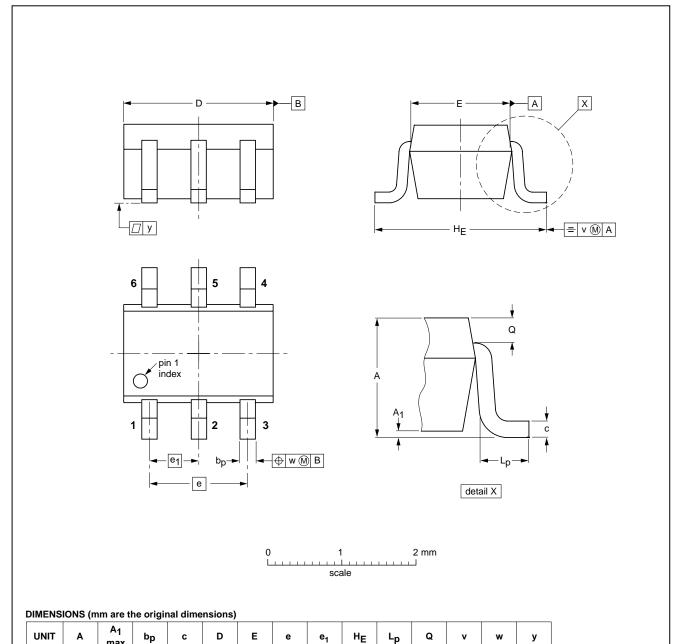
PNP general purpose double transistor

PUMT1

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT363



OUTLINE	REFERENCES		EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	1330E DATE
SOT363			SC-88		$ \ \ \bigoplus \big($	97-02-28

0.65

0.45 0.15 0.25 0.15

0.2

0.1

2001 Dec 19 4

0.25 0.10

0.30

0.20

1.1 0.8

0.1

 $\mathsf{m}\mathsf{m}$

2.2 1.8 1.35 1.15

1.3

NXP Semiconductors Product data sheet

PNP general purpose double transistor

PUMT1

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
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2001 Dec 19 5

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Customer notification

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Contact information

For additional information please visit: $\mbox{\bf http://www.nxp.com}$

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Printed in The Netherlands 613514/04/pp6 Date of release: 2001 Dec 19 Document order number: 9397 750 09226



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